

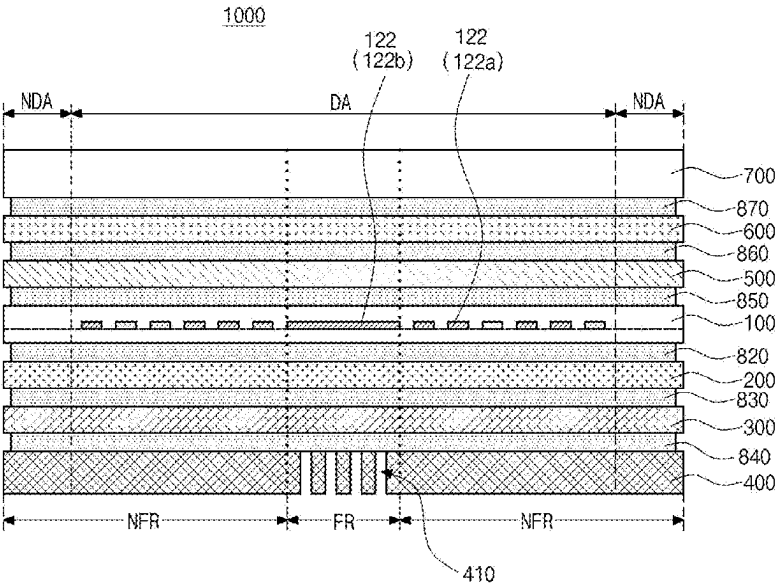
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Choi et al.

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(45) **Date of Patent:** **Aug. 19, 2025**

(54) **FOLDABLE DISPLAY DEVICE**
(71) Applicant: **LG DISPLAY CO., LTD.**, Seoul (KR)
(72) Inventors: **Kwang-Hyun Choi**, Paju-si (KR);
Min-Jic Lee, Paju-si (KR); **Ye-Seul Han**, Paju-si (KR); **Jeong-Ok Jo**, Paju-si (KR)
(73) Assignee: **LG Display Co., Ltd.**, Seoul (KR)
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H10K 102/00 (2023.01)
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CPC **H10K 59/126** (2023.02); **H10K 50/86** (2023.02); **H10K 77/111** (2023.02); **H10K 2102/311** (2023.02)
(58) **Field of Classification Search**
CPC H10K 59/126; H10K 50/86; H10K 77/111; H10K 2102/311
See application file for complete search history.

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Office Action dated Nov. 30, 2024 issued in Korean Patent Application No. 10-2021-0180260.
Primary Examiner — Mohsen Ahmadi
(74) Attorney, Agent, or Firm — Morgan, Lewis & Bockius LLP
(57) **ABSTRACT**
A foldable display device includes a display panel including a plurality of sub-pixels and having a first shield pattern in a non-folding region and a second shield pattern in a folding region; a cover window over the display panel, wherein an area of the second shield pattern is larger than an area of the first shield pattern.

14 Claims, 12 Drawing Sheets



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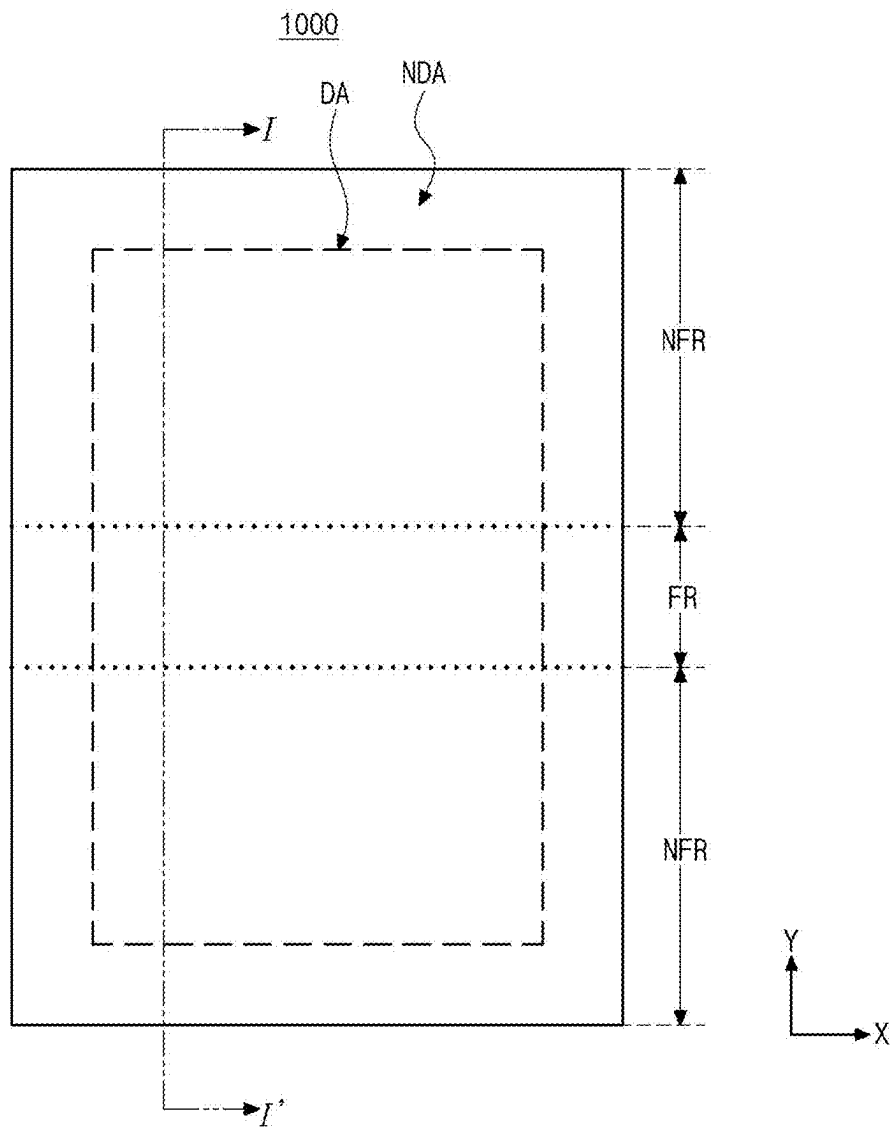


FIG. 1

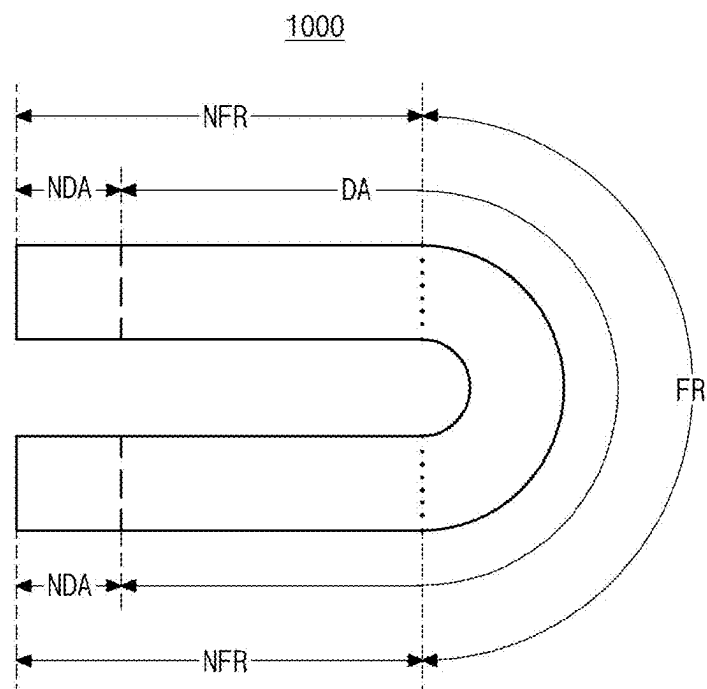


FIG. 2

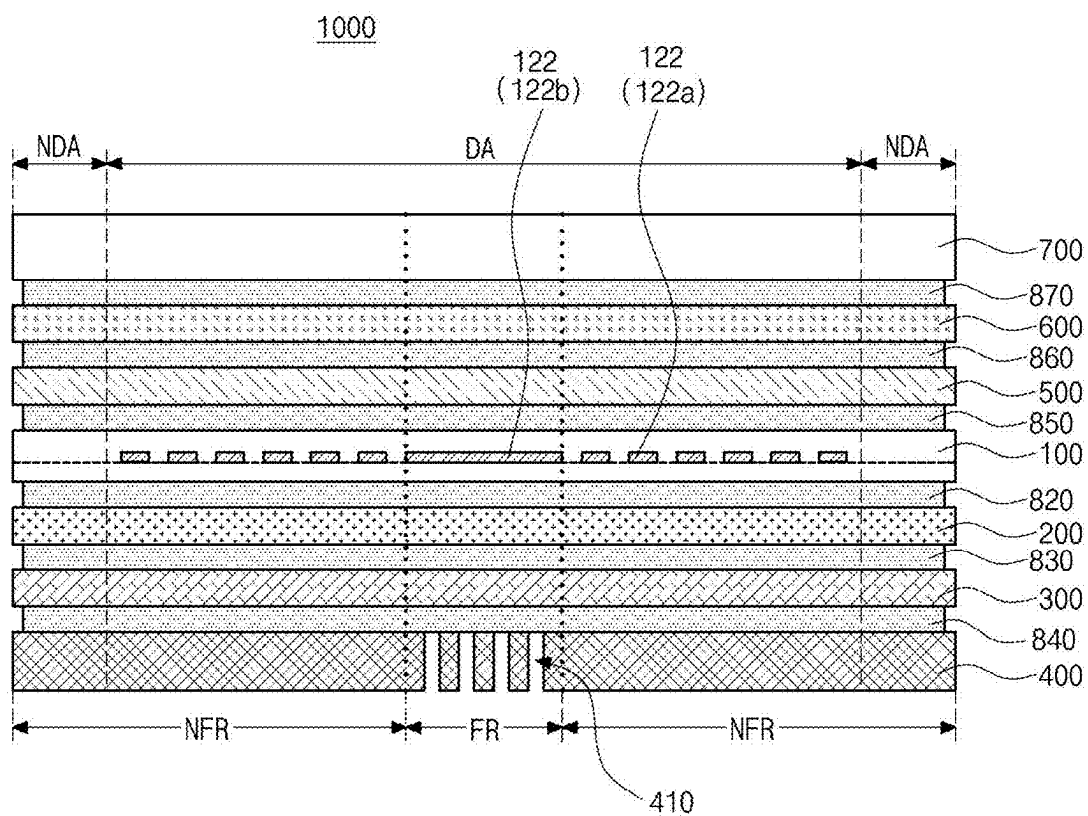


FIG. 3

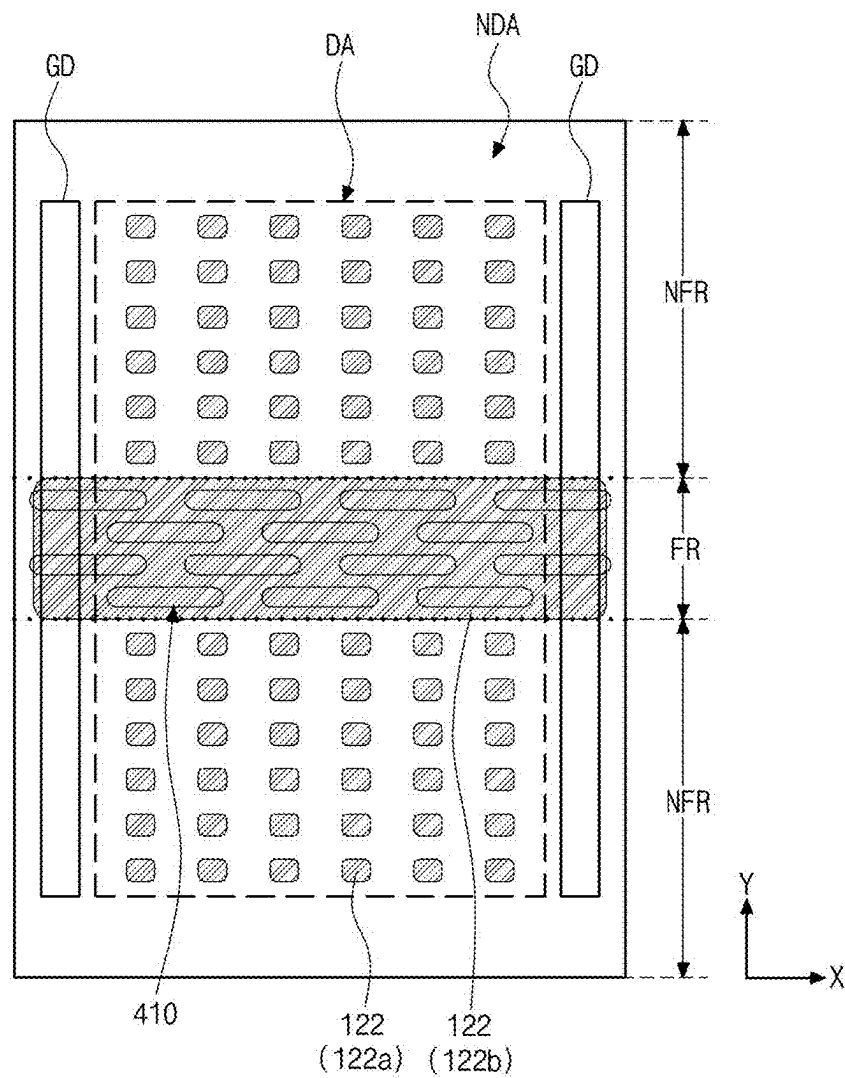


FIG. 4

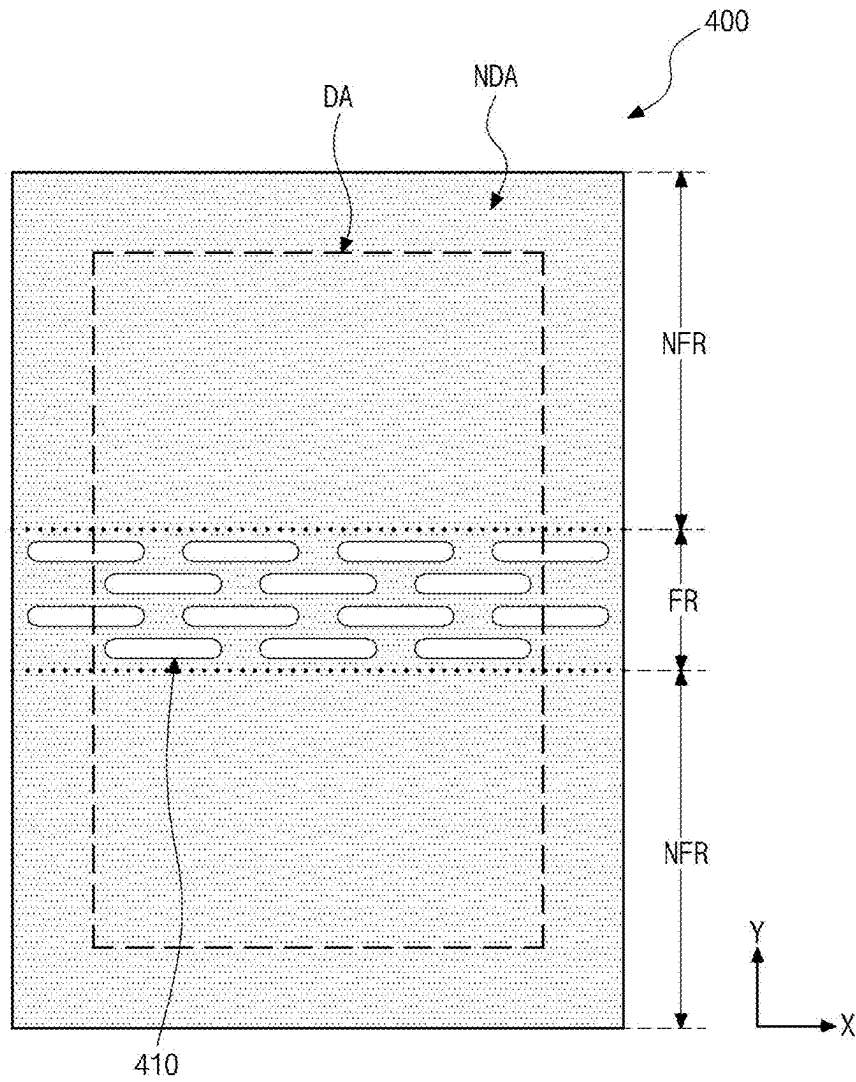


FIG. 5

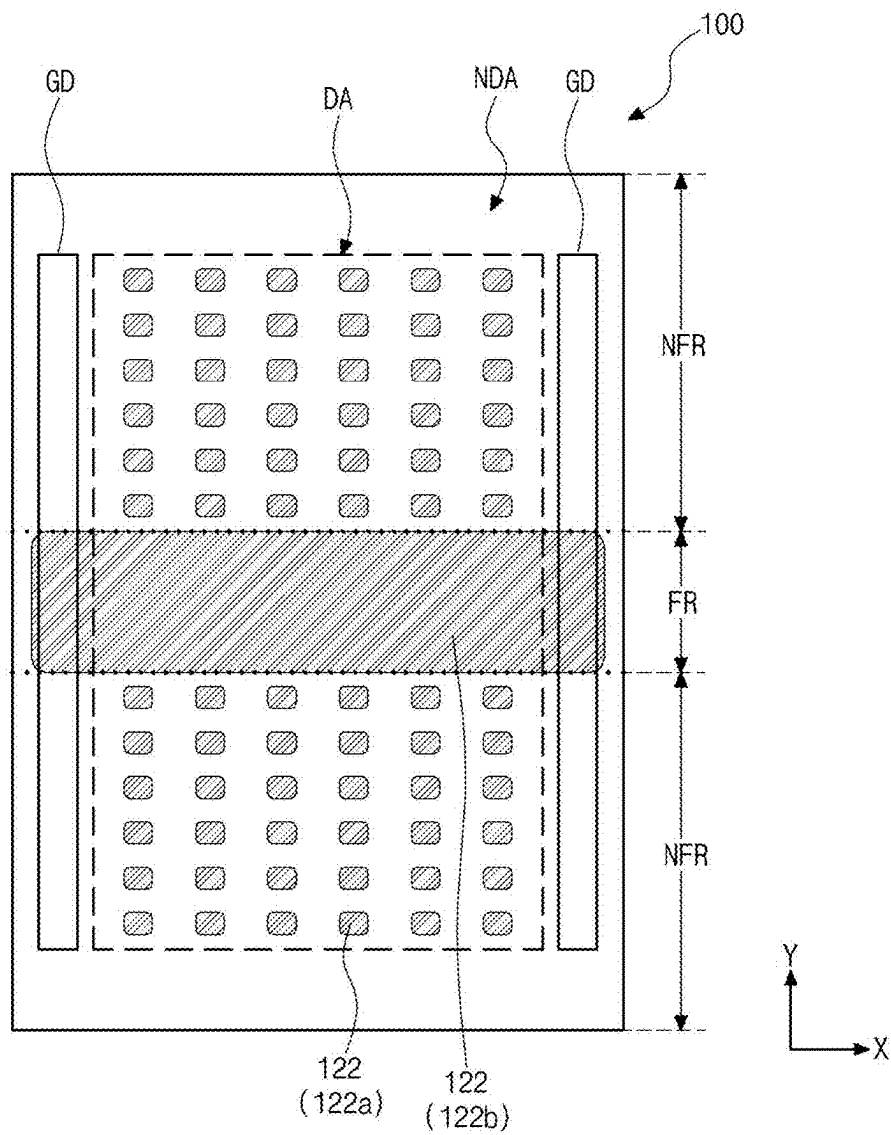


FIG. 6

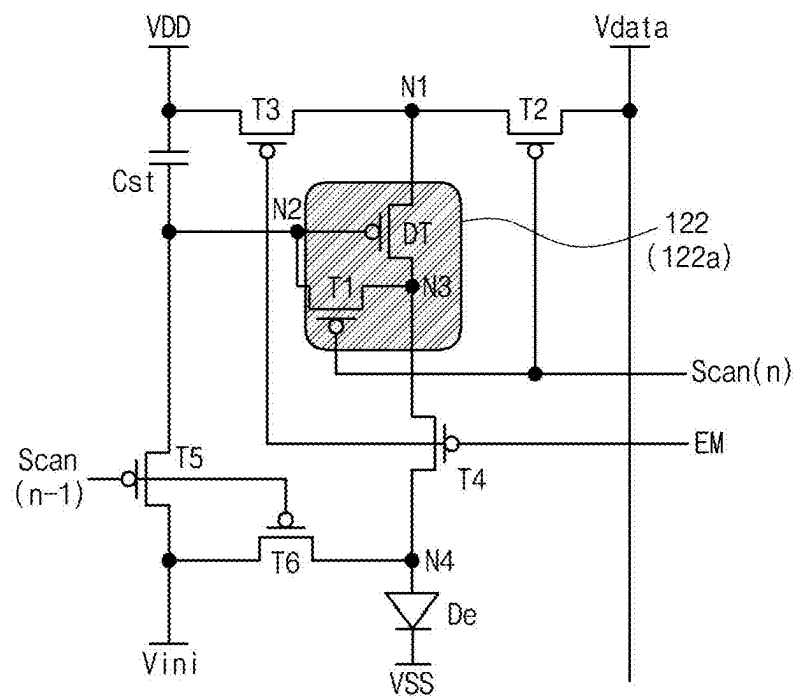


FIG. 7

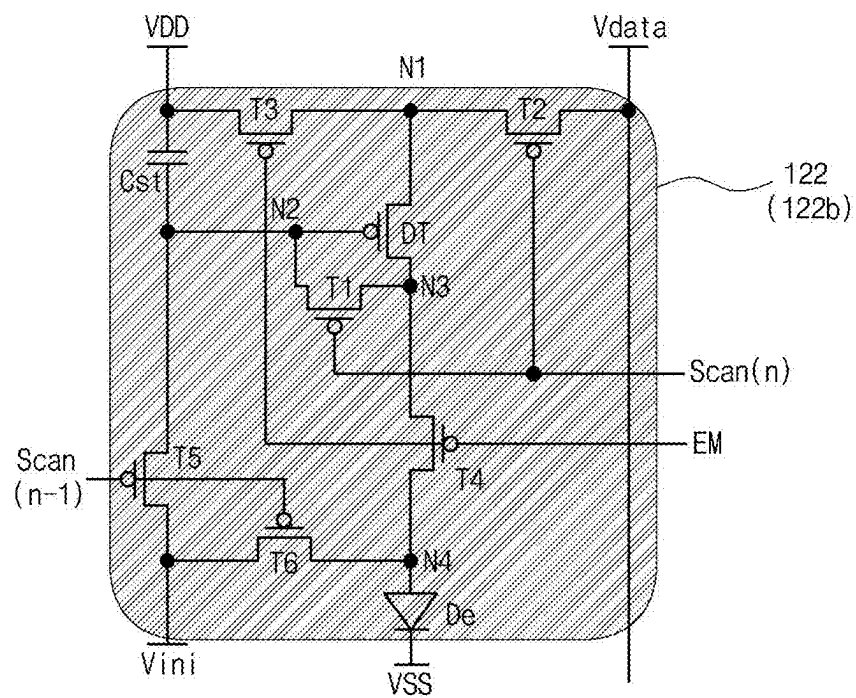


FIG. 8

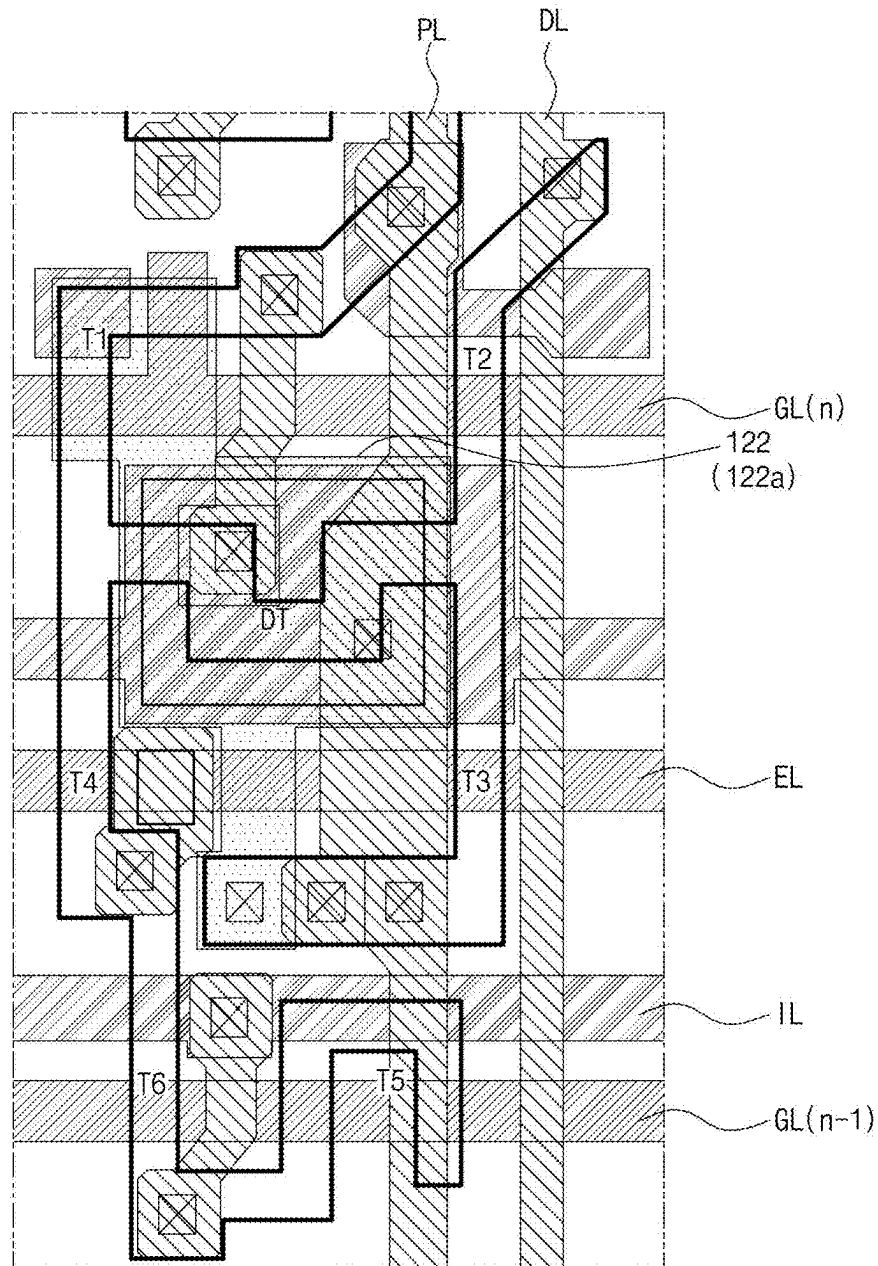


FIG. 9

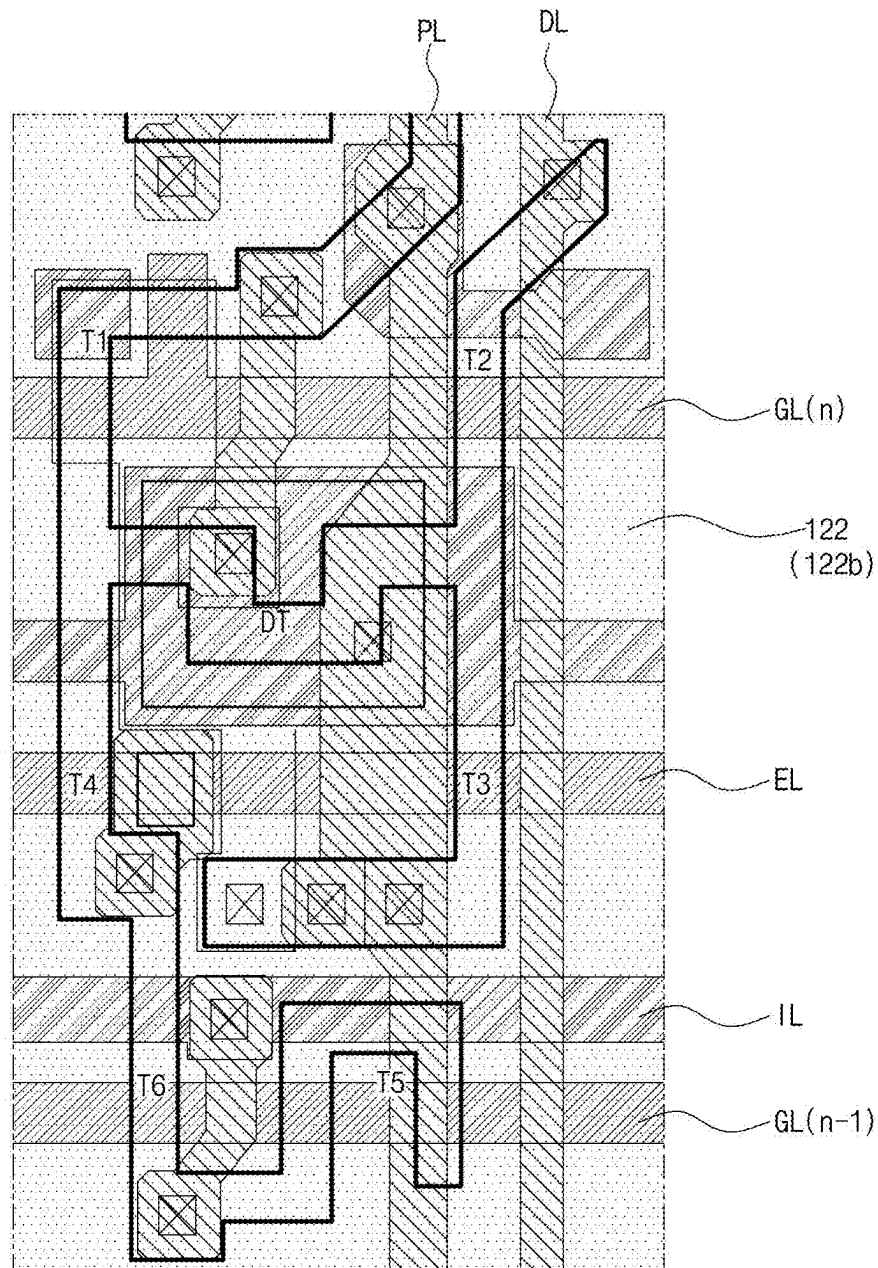


FIG. 10

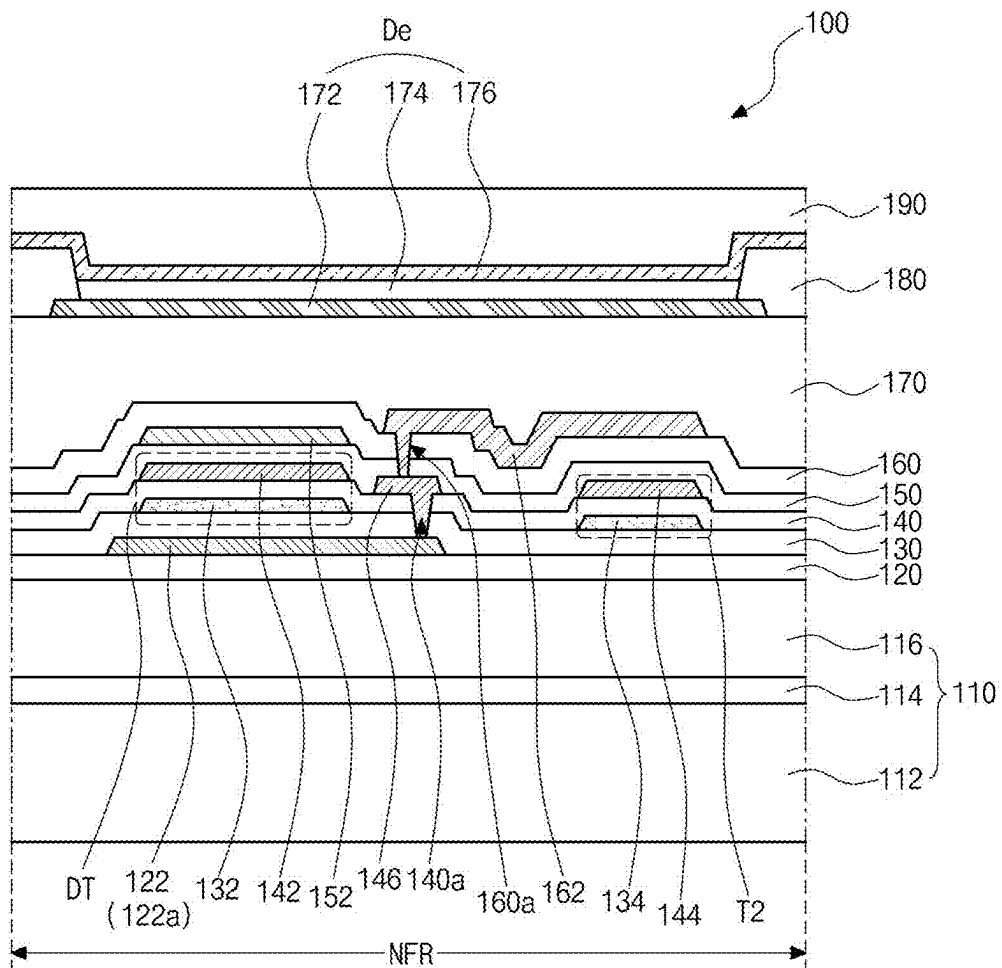


FIG. 11

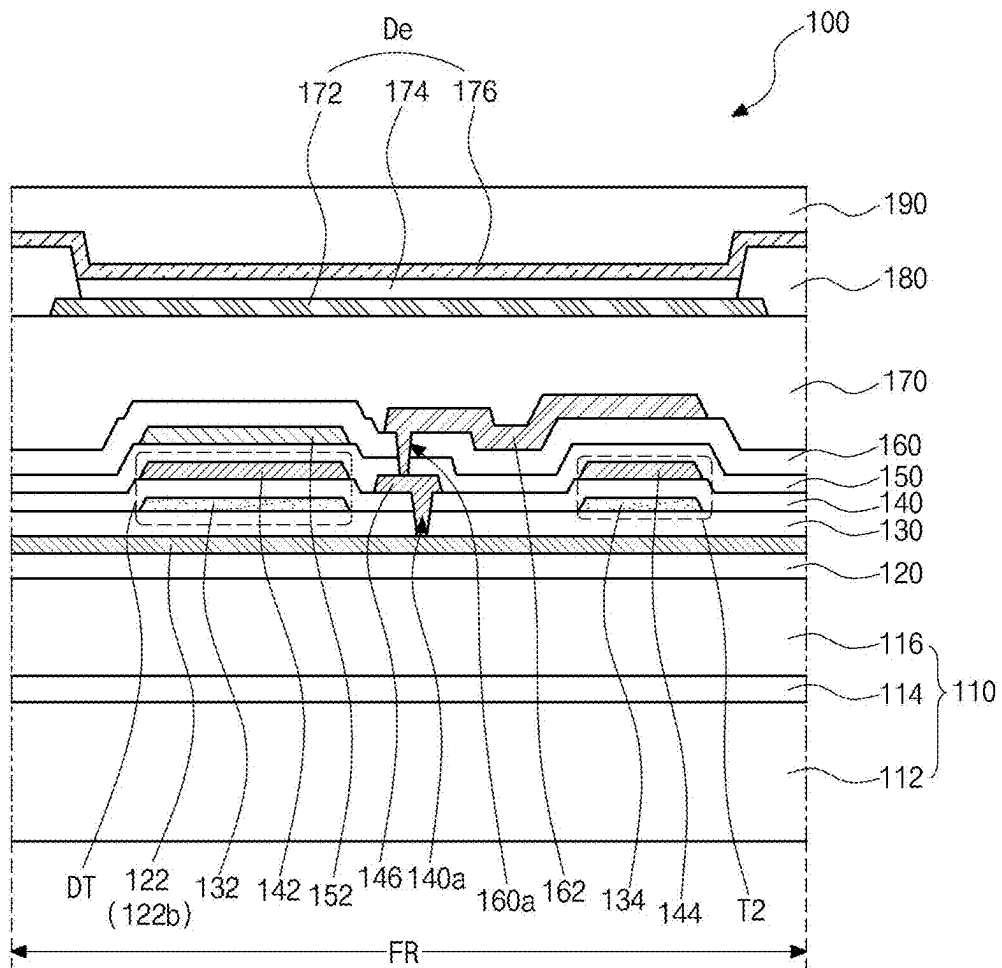


FIG. 12

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FOLDABLE DISPLAY DEVICE**CROSS-REFERENCE TO RELATED APPLICATION**

The present application claims the priority of Korean Patent Application No. 10-2021-0180260 filed on Dec. 16, 2021, which is hereby incorporated by reference in its entirety.

BACKGROUND**Technical Field**

The present disclosure relates to a foldable display device, and more particularly, to a foldable display device with improved durability.

Discussion of the Related Art

An electroluminescent display device, which is one of flat panel display devices, has a wide viewing angle as compared with a liquid crystal display device because it is self-luminous and is thin, light weight, and low in power consumption because a backlight unit is not necessary. In addition, an electroluminescent display device is driven by low voltages of direct current (DC) and has a fast response time. An electroluminescent display device is also resistant to external impacts and may be used in a wide range of temperatures because its components are solids. An electroluminescent display device may also be manufactured at low cost.

Recently, a foldable display device, which can be freely folded and unfolded by forming components of the electroluminescent display device on a flexible substrate, has been widely developed and applied to various fields.

The foldable display device is in an unfolded state when displaying an image to provide a wide screen and is in a folded state when not displaying an image to reduce the volume, thereby having advantages of convenient transportation and/or storage.

By the way, since the foldable display device is repeatedly folded and unfolded more than tens of thousands of times, improving durability is emerging as an important issue.

SUMMARY

Accordingly, embodiments of the present disclosure are directed to a foldable display device that substantially obviates one or more of the problems due to limitations and disadvantages described above.

An aspect of the present disclosure is to provide a foldable display device with the improved durability.

Additional features and aspects will be set forth in the description that follows, and in part will be apparent from the description, or may be learned by practice of the inventive concepts provided herein. Other features and aspects of the inventive concepts may be realized and attained by the structure particularly pointed out in the written description, or derivable therefrom, and the claims hereof as well as the appended drawings.

To achieve these and other aspects of the present disclosure, as embodied and broadly described herein, a foldable display device comprises a display panel including a plurality of sub-pixels and having a first shield pattern in a non-folding region and a second shield pattern in a folding

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region; a cover window over the display panel, wherein an area of the second shield pattern is larger than an area of the first shield pattern.

It is to be understood that both the foregoing general description and the following detailed description are exemplary and explanatory and are intended to provide further explanation of the inventive concepts as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

The accompanying drawings, which are included to provide a further understanding of the present disclosure and which are incorporated in and constitute a part of this application, illustrate aspects of the disclosure and together with the description serve to explain various principles of the present disclosure. In the drawings:

FIG. 1 is a schematic plan view of a foldable display device according to an embodiment of the present disclosure;

FIG. 2 is a schematic cross-sectional view of the foldable display device according to the embodiment of the present disclosure;

FIG. 3 is a schematic cross-sectional view corresponding to the line I-I';

FIG. 4 is a plan view schematically illustrating the display panel and the plate bottom of the foldable display device according to the embodiment of the present disclosure;

FIG. 5 is a plan view schematically illustrating the plate bottom of the foldable display device according to the embodiment of the present disclosure;

FIG. 6 is a plan view schematically illustrating the display panel of the foldable display device according to the embodiment of the present disclosure;

FIG. 7 is a circuit diagram illustrating a sub-pixel of the display panel in the non-folding region of the foldable display device according to the embodiment of the present disclosure;

FIG. 8 is a circuit diagram illustrating a sub-pixel of the display panel in the folding region of the foldable display device according to the embodiment of the present disclosure;

FIG. 9 is a plan view schematically illustrating the sub-pixel of the display panel in the non-folding region of the foldable display device according to the embodiment of the present disclosure;

FIG. 10 is a plan view schematically illustrating the sub-pixel of the display panel in the folding region of the foldable display device according to the embodiment of the present disclosure;

FIG. 11 is a cross-sectional view schematically illustrating the display panel in the non-folding region of the foldable display device according to the embodiment of the present disclosure; and

FIG. 12 is a cross-sectional view schematically illustrating the display panel in the folding region of the foldable display device according to the embodiment of the present disclosure.

DETAILED DESCRIPTION

Reference will now be made in detail to aspects of the disclosure, an example embodiments of which are illustrated in the accompanying drawings.

FIG. 1 is a schematic plan view of a foldable display device according to an embodiment of the present disclosure and shows an unfolded state, and FIG. 2 is a schematic

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cross-sectional view of the foldable display device according to the embodiment of the present disclosure and shows a folded state.

In FIG. 1 and FIG. 2, the foldable display device **1000** according to the embodiment of the present disclosure includes a folding region FR and a non-folding region NFR and is folded in a first direction (e.g., a Y-axis direction).

Specifically, the foldable display device **1000** according to the embodiment of the present disclosure includes respective non-folding regions NFR at both sides of the folding region FR facing each other along the first direction (e.g., the Y-axis direction) such that one folding region FR is disposed between two non-folding regions NFR along the first direction (e.g., the Y-axis direction).

In addition, the foldable display device **1000** includes a display area DA displaying an image and a non-display area NDA surrounding the display area DA. A plurality of sub-pixels is disposed in the display area DA to implement an image. Pads, signal lines, and driving parts are disposed in the non-display area NDA to provide signals to the plurality of sub-pixels.

When implementing the folding state, the foldable display device **1000** of the present disclosure can be out-folded in which a display surface is exposed to the outside. However, the present disclosure is not limited thereto. Alternatively, the foldable display device **1000** of the present disclosure can be in-folded in which the display surface is hidden inside.

FIG. 3 is a schematic cross-sectional view of the foldable display device according to the embodiment of the present disclosure and shows the cross-section corresponding to the line I-I'.

In FIG. 3, the foldable display device **1000** according to the embodiment of the present disclosure includes a display panel **100**, a back plate **200**, a plate top **300**, a plate bottom **400**, a polarizing plate **500**, a decoration film **600**, and a cover window **700**.

The display panel **100** includes the plurality of sub-pixels in the display area DA and displays an image. The display panel **100** of the present disclosure can be an organic light-emitting diode panel.

Meanwhile, a shield pattern **122** is formed in the display area DA of the display panel **100**. The shield pattern **122** includes at least one first shield pattern **122a** disposed in the non-folding region NFR and at least one second shield pattern **122b** disposed in the folding region FR.

Here, the area of the at least one second shield pattern **122b** is larger than the area of the at least one first shield pattern **122a**. More particularly, the first shield pattern **122a** can be formed to correspond to each sub-pixel, and the plurality of first shield patterns **122a** can be disposed in the non-folding region NFR. On the other hand, the second shield pattern **122b** can be formed over substantially an entire surface of the folding region FR, and one second shield pattern **122b** can be disposed in the folding region FR.

The first and second shield patterns **122a** and **122b** will be described in detail later.

Meanwhile, to improve the durability and maintain the shape of the foldable display device **1000**, the back plate **200**, the plate top **300**, and the plate bottom **400** are provided under the display panel **100** and are sequentially disposed from the bottom surface of the display panel **100**.

The back plate **200** can be formed of an organic material having excellent molding characteristics. For example, the back plate **200** can be formed of polyimide, but is not limited thereto.

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The plate top **300** and the plate bottom **400** can be formed of a metal material. The thickness of the plate bottom **400**, which is exposed to the outside, can be thicker than the thickness of the plate top **300**. For example, the plate top **300** can be formed of SUS301 having relatively high hardness, and the plate bottom **400** can be formed of SUS316 having relatively high corrosion resistance and acid resistance. However, the present disclosure is not limited thereto.

To improve the folding characteristics, the plate bottom **400** can include a plurality of openings **410** in the folding region FR. The plurality of openings **410** can be provided to penetrate upper and lower surfaces of the plate bottom **400**.

Next, the polarizing plate **500** is disposed on the display panel **100**. The polarizing plate **500** can be a circular polarizing plate including a linear polarizer and a quarter wave plate and can prevent the external light from being reflected by the display panel **100** and output to the outside.

The decoration film **600** is disposed on the polarizing plate **500**. The decoration film **600** can serve as a black matrix that blocks light in an undesired area.

The cover window **700** is disposed on the decoration film **600**. The cover window **700** protects the display panel **100** from impacts, moisture, or heat from the outside and can be formed of transparent glass or plastic. For example, the cover window **700** can be formed of plastic such as polymethylmethacrylate (PMMA), polyimide (PI), or polyethyleneterephthalate (PET) or formed of ultra-thin glass (UTG), but is not limited thereto.

First, second, third, fourth, fifth, and sixth adhesive members **820**, **830**, **840**, **850**, **860**, and **870** are provided between adjacent components of the display panel **100**, the back plate **200**, the plate top **300**, the plate bottom **400**, the polarizing plate **500**, the decoration film **600**, and the cover window **700**.

Specifically, the first adhesive member **820** is provided between the display panel **100** and the back plate **200**, the second adhesive member **830** is provided between the back plate **200** and the plate top **300**, the third adhesive member **840** is provided between the plate top **300** and the plate bottom **400**, the fourth adhesive member **850** is provided between the display panel **100** and the polarizing plate **500**, the fifth adhesive member **860** is provided between the polarizing plate **500** and the decoration film **600**, and the sixth adhesive member **870** is provided between the decoration film **600** and the cover window **700**.

The first, second, third, fourth, fifth, and sixth adhesive members **820**, **830**, **840**, **850**, **860**, and **870** can be optically clear adhesive (OCA) or pressure sensitive adhesive (PSA).

As described above, in the foldable display device **1000** according to the embodiment of the present disclosure, to improve the durability and maintain the shape, the back plate **200**, the plate top **300**, and the plate bottom **400** are provided under the display panel **100**.

In this case, in order to improve the folding characteristics of the plate bottom **400** that is relatively thick and formed of a metal material, the plurality of openings **410** is formed in the folding region FR of the plate bottom **400**.

By the way, the durability of the folding region FR can be lower than the non-folding region NFR due to the openings **410**. For example, when evaluating the impact resistance, the durability of the folding region FR is reduced to about 1/2 or less compared to the non-folding region NFR.

Accordingly, the durability can be improved by forming the second shield pattern **122b** over substantially the entire surface of the folding region FR of the display panel **100**.

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The configurations of the display panel **100** and the plate bottom **400** will be described in detail with reference to FIGS. **4** to **6**.

FIG. **4** is a plan view schematically illustrating the display panel and the plate bottom of the foldable display device according to the embodiment of the present disclosure, FIG. **5** is a plan view schematically illustrating the plate bottom of the foldable display device according to the embodiment of the present disclosure, and FIG. **6** is a plan view schematically illustrating the display panel of the foldable display device according to the embodiment of the present disclosure.

In FIGS. **4** to **6**, the plate bottom **400** of the foldable display device according to the embodiment of the present disclosure includes the plurality of openings **410** in the folding region FR.

The openings **410** each have a length of a direction perpendicular to a folding direction longer than a length of the folding direction. That is, each of the openings **410** has a length of a second direction (e.g., an X-axis direction) longer than a length of the first direction (e.g., the Y-axis direction). In other words, a length of a respective opening **410** in the second direction (e.g., the X-axis direction) is longer than a length of the opening **410** in the first direction (e.g., the Y-axis direction).

The openings **410** can be formed to extend from the display area DA to the non-display area NDA and formed not only in the display area DA but also in the non-display area.

Here, the shapes and numbers of the openings **410** are not limited to those illustrated and can be changed.

Next, the display panel **100** includes the shield pattern **122** in the display area DA. The shield pattern **122** includes the plurality of first shield patterns **122a** in the non-folding region NFR and one second shield pattern **122b** in the folding region FR.

Here, the second shield pattern **122b** overlaps the plurality of openings **410**.

The plurality of first shield patterns **122a** is formed to correspond to the plurality of sub-pixels, respectively. On the other hand, the second shield pattern **122b** is formed over substantially the entire surface of the folding region FR and corresponds to all the sub-pixels of the folding region FR. The area of the second shield pattern **122b** is larger than the area of each of the first shield patterns **122a**. In addition, the display panel **100** includes at least one gate driving part GD in the non-display area NDA. In this case, the gate driving part GD can extend along the first direction (e.g., the Y-axis direction) and can be disposed in the folding region FR and the non-folding region NFR. Further, the gate driving part GD can be disposed in each of two portions of the non-display area NDA facing each other along the second direction (e.g., the X-axis direction).

The gate driving part GD can include a plurality of transistors, capacitors, and lines and can be provided on a substrate of the display panel **100** in the form of a gate-in-panel.

At this time, the second shield pattern **122b** can extend into the non-display area NDA and can overlap the gate driving part GD.

Meanwhile, the plurality of openings **410** can overlap the gate driving part GD.

As described above, in the foldable display device according to the embodiment of the present disclosure, the second shield pattern **122b** is provided over substantially the entire surface of the folding region FR of the display panel **100**, so that the durability can be improved.

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Meanwhile, if the first shield pattern **122a** is formed over the entire surface of the non-folding region NFR, the durability of the foldable display device can be further improved. However, in this case, the parasitic capacitance of the data line or the like increases, and the driving characteristics are degraded.

Accordingly, the shield pattern **122** is differently designed in the folding region FR and the non-folding region NFR. That is, in the folding region FR, the second shield pattern **122b** is formed over substantially the entire surface, and the second shield pattern **122b** is formed in entirety of each sub-pixel. On the other hand, the first shield pattern **122a** is formed only in a portion of each sub-pixel.

The configurations of the sub-pixels of the display panel according to the embodiment of the present disclosure will be described with reference to FIGS. **7** to **10**.

FIG. **7** is a circuit diagram illustrating a sub-pixel of the display panel in the non-folding region of the foldable display device according to the embodiment of the present disclosure, FIG. **8** is a circuit diagram illustrating a sub-pixel of the display panel in the folding region of the foldable display device according to the embodiment of the present disclosure, and FIG. **7** and FIG. **8** also show the first and second shield patterns, respectively. In addition, FIG. **9** is a plan view schematically illustrating the sub-pixel of the display panel in the non-folding region of the foldable display device according to the embodiment of the present disclosure, and FIG. **10** is a plan view schematically illustrating the sub-pixel of the display panel in the folding region of the foldable display device according to the embodiment of the present disclosure.

In FIGS. **7** to **10**, each sub-pixel of the display panel of the foldable display device according to the embodiment of the present disclosure includes a driving transistor DT, first, second, third, fourth, fifth, and sixth transistors T1, T2, T3, T4, T5, and T6, a storage capacitor Cst, and a light-emitting diode De.

For example, the driving transistor DT and the first, second, third, fourth, fifth, and sixth transistors T1, T2, T3, T4, T5, and T6 can be P-type. However, the present disclosure is not limited thereto. Alternatively, the driving transistor DT and the first, second, third, fourth, fifth, and sixth transistors T1, T2, T3, T4, T5, and T6 can be N-type.

Here, the driving transistor DT can be connected to first, second, and third nodes N1, N2, and N3, the storage capacitor Cst can be connected to the second node N2 and a high potential voltage VDD, and the light-emitting diode De can be connected to a fourth node N4 and a low potential voltage VSS.

The driving transistor DT is switched according to a voltage of a first electrode of the storage capacitor Cst, that is, the second node N2, and each of the first, second, third, fourth, fifth, and sixth transistors T1, T2, T3, T4, T5, and T6 is switched according to one of an nth gate voltage Scan(n), an (n-1)th gate voltage Scan(n-1), and an emission voltage EM. Here, n is a natural number.

Specifically, the driving transistor DT can be switched according to the voltage of the first electrode of the storage capacitor Cst. A gate electrode of the driving transistor DT can be connected to the first electrode of the storage capacitor Cst, a drain electrode of the first transistor T1, and a source electrode of the fifth transistor T5. A source electrode of the driving transistor DT can be connected to a drain electrode of the second transistor T2 and a source electrode of the third transistor T3. A drain electrode of the driving

transistor DT can be connected to a source electrode of the first transistor T1 and a source electrode of the fourth transistor T4.

The first transistor T1 can be switched according to the nth gate voltage Scan(n). A gate electrode of the first transistor T1 can be connected to an nth gate line GL(n) to receive the nth gate voltage Scan(n). The source electrode of the first transistor T1 can be connected to the drain electrode of the driving transistor DT and the source electrode of the fourth transistor T4. The drain electrode of the first transistor T1 can be connected to the first electrode of the storage capacitor Cst, the gate electrode of the driving transistor DT, and the source electrode of the fifth transistor T5.

The second transistor T2, which is a switching transistor, can be switched according to the nth gate voltage Scan(n) to transmit a data voltage Vdata. A gate electrode of the second transistor T2 can be connected to the nth gate line GL(n) to receive the nth gate voltage Scan(n). A source electrode of the second transistor T2 can be connected to a data line DL to transmit the data voltage Vdata. The drain electrode of the second transistor T2 can be connected to the source electrode of the driving transistor DT and the source electrode of the third transistor T3.

The third transistor T3 can be switched according to the emission voltage EM. A gate electrode of the third transistor T3 can be connected to an emission line EL to receive the emission voltage EM. The source electrode of the third transistor T3 can be connected to the source electrode of the driving transistor DT and the drain electrode of the second transistor T2. A drain electrode of the third transistor T3 can be connected to a second electrode of the storage capacitor Cst and connected to a power line PL to receive a high potential voltage VDD.

The fourth transistor T4 can be switched according to the emission voltage EM. A gate electrode of the fourth transistor T4 can be connected to the emission line EL to receive the emission voltage EM. The source electrode of the fourth transistor T4 can be connected to the drain electrode of the driving transistor DT and the source electrode of the first transistor T1. A drain electrode of the fourth transistor T4 can be connected to an anode of the light-emitting diode De.

The fifth transistor T5 can be switched according to the (n-1)th gate voltage Scan(n-1). A gate electrode of the fifth transistor T5 can be connected to an (n-1)th gate line GL(n-1) to receive the (n-1)th gate voltage Scan(n-1). The source electrode of the fifth transistor T5 can be connected to the gate electrode of the driving transistor DT, the first electrode of the storage capacitor Cst, and the drain electrode of the first transistor T1. A drain electrode of the fifth transistor T5 can be connected to a drain electrode of the sixth transistor T6 and connected to an initialization line IL to receive an initialization voltage Vini.

The sixth transistor T6 can be switched according to the (n-1)th gate voltage Scan(n-1). A gate electrode of the sixth transistor T6 can be connected to the (n-1)th gate line GL(n-1) to receive the (n-1)th gate voltage Scan(n-1). A source electrode of the sixth transistor T6 can be connected to the drain electrode of the fourth transistor T4 and the anode of the light-emitting diode De. The drain electrode of the sixth transistor T6 can be connected to the drain electrode of the fifth transistor T5 and connected to the initialization line IL to receive the initialization voltage Vini.

The storage capacitor Cst can be connected between the high potential voltage VDD and the driving transistor DT. In particular, the first electrode of the storage capacitor Cst can be connected to the gate electrode of the driving transistor DT, the drain electrode of the first transistor T1,

and the source electrode of the fifth transistor T5. The second electrode of the storage capacitor Cst can be connected to the drain electrode of the third transistor T3 and connected to the power line PL to receive the high potential voltage VDD.

The light-emitting diode De can be connected between the fourth transistor T4 and the low potential voltage VSS to emit light with luminance proportional to a current of the driving transistor DT. The anode of the light-emitting diode De can be connected to the drain electrode of the fourth transistor T4. The cathode of the light-emitting diode De can receive the low potential voltage VSS. Further, the anode of the light-emitting diode De can be connected to the source electrode of the sixth transistor T6.

Meanwhile, in the display panel according to the embodiment of the present disclosure, the shield pattern 122 is formed to correspond to the sub-pixel. The shield pattern 122 includes the first shield pattern 122a disposed in the non-folding region and the second shield pattern 122b disposed in the folding region.

The first shield pattern 122a of the non-folding region overlaps the driving transistor DT and the first transistor T1. Alternatively, the first shield pattern 122a can overlap only the driving transistor DT.

On the other hand, the second shield pattern 122b of the folding region overlaps the driving transistor DT and the first, second, third, fourth, fifth and sixth transistors T1, T2, T3, T4, T5, and T6. In addition, the second shield pattern 122b further overlaps the storage capacitor Cst and the light-emitting diode De and also overlaps the plurality of lines GL(n), GL(n-1), DL, PL, EL, and IL.

The cross-sectional configurations of the display panel according to the embodiment of the present disclosure will be described with reference to FIG. 11 and FIG. 12.

FIG. 11 is a cross-sectional view schematically illustrating the display panel in the non-folding region of the foldable display device according to the embodiment of the present disclosure, and FIG. 12 is a cross-sectional view schematically illustrating the display panel in the folding region of the foldable display device according to the embodiment of the present disclosure.

In FIG. 11 and FIG. 12, the display panel 100 of the present disclosure includes the plurality of transistors DT and T2 and the light-emitting diode De on a flexible substrate 110. Here, the plurality of transistors DT and T2 can be the driving transistor DT and the second transistor T2, which is the switching transistor, of FIGS. 7 and 8.

More particularly, a first buffer layer 120 is formed on the flexible substrate 110. The flexible substrate 110 can be formed of a material having flexibility. The flexible substrate 110 can include first, second, and third base layers 112, 114, and 116 sequentially disposed from the bottom. Accordingly, the second base layer 114 can be disposed between the first and third base layers 112 and 116.

The first and third base layers 112 and 116 can be formed of an organic material, and the second base layer 114 can be formed of an inorganic material. For example, the first and third base layers 112 and 116 can be formed of polyimide, and the second base layer 114 can be formed of silicon oxide (SiO₂) or silicon nitride (SiN_x).

Here, thicknesses of the first and third base layers 112 and 116 can be thicker than a thickness of the second base layer 114. In addition, the thickness of the first base layer 112 can be thicker than the thickness of the third base layer 116. That is, the thickness of the third base layer 116 can be greater than the thickness of the second base layer 114 and smaller than the thickness of the first base layer 112.

The first buffer layer **120** can be formed over substantially an entire surface of the flexible substrate **110**. The first buffer layer **120** can be formed of an inorganic insulating material, such as silicon oxide (SiO_2) or silicon nitride (SiNx), and can have a single-layer structure or a multiple-layer structure.

The shield pattern **122** is formed on the first buffer layer **120**. The shield pattern **122** includes the first shield pattern **122a** disposed in the non-folding region NFR and the second shield pattern **122b** disposed in the folding region FR.

In the non-folding region NFR, the first shield pattern **122a** overlaps the driving transistor DT and does not overlap the second transistor T2.

Alternatively, in the folding region FR, the second shield pattern **122b** overlaps the driving transistor DT and the second transistor T2.

Further, as described above, in the non-folding region NFR, the first shield pattern **122a** overlaps the first transistor T1 of FIG. 7, and in the folding region FR, the second shield pattern **122b** overlaps the first, third, fourth, fifth, and sixth transistors T1, T3, T4, T5, and T6 of FIG. 8.

The shield pattern **122**, that is, the first and second shield patterns **122a** and **122b** can be formed of a metal material, for example, at least one of aluminum (Al), copper (Cu), molybdenum (Mo), chromium (Cr), nickel (Ni), tungsten (W), or their alloys and can have a single-layer structure or a multiple-layer structure.

A second buffer layer **130** is formed on the first and second shield patterns **122a** and **122b** over substantially the entire surface of the flexible substrate **110**. The second buffer layer **130** can be formed of an inorganic insulating material, such as silicon oxide (SiO_2) or silicon nitride (SiNx), and can have a single-layer structure or a multiple-layer structure.

First and second semiconductor layers **132** and **134** are formed on the second buffer layer **130**. In the non-folding region NFR, the first semiconductor layer **132** is disposed right over the first shield pattern **122a** and overlaps the first shield pattern **122a**, and the second semiconductor layer **134** is spaced apart from the first shield pattern **122a** and does not overlap the first shield pattern **122a**. On the other hand, in the folding region FR, the first and second semiconductor layers **132** and **134** are disposed right over the second shield pattern **122b** and overlap the second shield pattern **122b**.

The first and second semiconductor layers **132** and **134** can be formed of an oxide semiconductor material. Alternatively, the first and second semiconductor layers **132** and **134** can be formed of polycrystalline silicon.

A gate insulation layer **140** is formed on the first and second semiconductor layers **132** and **134** over substantially the entire surface of the flexible substrate **110**. The gate insulation layer **140** can be formed of an inorganic insulating material, such as silicon oxide (SiO_2) or silicon nitride (SiNx), and can have a single-layer structure or a multiple-layer structure.

The gate insulation layer **140** and the second buffer layer **130** have a first contact hole **140a** exposing the shield pattern **122**, that is, each of the first and second shield patterns **122a** and **122b**, thereunder.

First and second gate electrodes **142** and **144** are formed on the gate insulation layer **140**. The first gate electrode **142** is disposed right over the first semiconductor layer **132** and overlaps the first semiconductor layer **132**. The second gate electrode **144** is disposed right over the second semiconductor layer **134** and overlaps the second semiconductor layer **134**. The first and second gate electrodes **142** and **144** can be formed of a metal material, for example, at least one

of aluminum (Al), copper (Cu), molybdenum (Mo), chromium (Cr), nickel (Ni), tungsten (W), or their alloys and can have a single-layer structure or a multiple-layer structure.

A connection pattern **146** is formed on the gate insulation layer **140**. The connection pattern **146** can be formed of the same material as the first and second gate electrodes **142** and **144**. The connection pattern **146** is in direct contact with the shield pattern **122** through the first contact hole **140a**.

A first interlayer insulation layer **150** is formed on the first and second gate electrodes **142** and **144** and the connection pattern **146** over substantially the entire surface of the flexible substrate **110**. The first interlayer insulation layer **150** can be formed of an inorganic insulating material, such as silicon oxide (SiO_2) or silicon nitride (SiNx).

A capacitor electrode **152** of a metal material is formed on the first interlayer insulation layer **150**. The capacitor electrode **152** can overlap the first gate electrode **142**.

A second interlayer insulation layer **160** is formed on the capacitor electrode **152** over substantially the entire surface of the flexible substrate **110**. The second interlayer insulation layer **160** can be formed of an inorganic insulating material, such as silicon oxide (SiO_2) or silicon nitride (SiNx).

The second interlayer insulation layer **160** and the first interlayer insulation layer **150** have a second contact hole **160a** exposing the connection pattern **146** thereunder.

A power line **162** of a metal material is formed on the second interlayer insulation layer **160**. The power line **162** is in direct contact with the connection pattern **146** through the second contact hole **160a**. Accordingly, the power line **162** is electrically connected to the shield pattern **122** through the connection pattern **146**.

The power line **162** can overlap the second gate electrode **144** and can be spaced apart from the first gate electrode **142**.

In addition, although not shown in the figure, first source and first drain electrodes and second source and second drain electrodes are further formed on the second semiconductor layer **134**. The first source and first drain electrodes and second source and second drain electrodes can be formed of the same material as the power line **162**.

The first semiconductor layer **132**, the first gate electrode **142**, and the first source and first drain electrodes constitute the driving transistor DT. The second semiconductor layer **134**, the second gate electrode **144**, and the second source and second drain electrodes constitute the second transistor T2.

A planarization layer **170** is formed on the power line **162**. The planarization layer **170** is formed over substantially the entire surface of the flexible substrate **110** and has a flat top surface, thereby removing step differences due to the layers thereunder. The planarization layer **170** can be formed of an organic insulating material. For example, the organic insulating material can be photo acrylic, but is not limited thereto.

A first electrode **172** is formed on the planarization layer **170**. The first electrode **172** can be formed of a conductive material having relatively high work function. For example, the first electrode **172** can be formed of a transparent conductive material, such as indium tin oxide (ITO) or indium zinc oxide (IZO).

In addition, the first electrode **172** can further include a reflection layer. For example, the reflection layer can be formed of aluminum-palladium-copper (APC) alloy, but is not limited thereto.

A bank layer **180** is formed on the first electrode **172**. The bank layer **180** covers edges of the first electrode **172** and exposes a central portion of the first electrode **172**. The bank layer **180** can be formed of an organic insulating material.

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A light-emitting layer **174** is formed on the first electrode **172** exposed by the bank layer **180**.

Although not shown in the figure, the light-emitting layer **174** can include a hole auxiliary layer, a light-emitting material layer, and an electron auxiliary layer sequentially stacked from a top surface of the first electrode **172**. The hole auxiliary layer can include at least one of a hole injecting layer (HIL) and a hole transporting layer (HTL). The electrode auxiliary layer can include at least one of an electron transporting layer (ETL) and an electrode injecting layer (EIL).

A second electrode **176** is formed on the light-emitting layer **174**. The second electrode **176** covers the bank layer **180**. The second electrode **176** can be formed over substantially the entire surface of the flexible substrate **110** and can be in contact with top and side surfaces of the bank layer **180**. The second electrode **176** can be formed of a conductive material having relatively low work function. For example, the second electrode **176** can be formed of aluminum (Al), magnesium (Mg), silver (Ag), or an alloy thereof, but is not limited thereto.

The first electrode **172**, the light-emitting layer **174**, and the second electrode **176** constitute the light-emitting diode.

An encapsulation layer **190** is formed on the second electrode **176** over substantially the entire surface of the flexible substrate **110**. The encapsulation layer **190** can be formed of an organic layer, an inorganic layer, or organic and inorganic layers alternately stacked.

As described above, in the foldable display device according to the embodiment of the present disclosure, the second shield pattern **122b** is formed over substantially the whole of each sub-pixel of the folding region FR, thereby improving the durability. On the other hand, the first shield pattern **122a** is formed only in a portion of each sub-pixel of the non-folding region NFR, so that it is possible to prevent deterioration of the driving characteristics due to the parasitic capacitance.

Here, in each sub-pixel, when the threshold voltages V_{th} of the driving transistor DT and the first transistor T1 are changed, the current variability of the light-emitting diode

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driving transistor DT and the first, second, third, fourth, fifth, and sixth transistors T1, T2, T3, T4, T5, and T6 of each sub-pixel.

Table 1 shows data of the parasitic capacitance of the data line (Data Line Cap.) and data rising time in the foldable display device according to the embodiment of the present disclosure and shows data of a foldable display device according to the comparative example together. Here, in the foldable display device according to the comparative example, the shield pattern is formed over substantially the entire surface of the non-folding region as well as the folding region.

TABLE 1

	Embodiment	Comparative example	Decrease rate
Data Line Cap.	75.183 pF	100.35 pF	25.07%
Data Rising Time	0.298 μ s	0.390 μ s	23.69%

As shown in Table 1, it can be seen that the parasitic capacitance of the data line in the embodiment of the present disclosure is decreased by about 25.07% compared to the comparative example, and thus, the data rising time is also decreased by 23.69%.

Accordingly, in the present disclosure, the shield pattern is designed differently in the folding region and the non-folding region, so that it is possible to prevent deterioration of the driving characteristics due to the parasitic capacitance.

Meanwhile, a change in characteristics of the transistors according to folding evaluation will be described with reference to Table 2.

Table 2 shows the fluctuation range ΔV_{th} of the threshold voltage V_{th} of the driving transistor DT and the switching transistor ST with respect to the presence or absence of the shield pattern thereunder, and shows data according to the radius of curvature and the number of foldings. Here, a smaller radius of curvature means more folding, and the switching transistor ST corresponds to the second transistor T2 of FIG. 7 and FIG. 8.

TABLE 2

Radius of curvature								
3.0R				4.0R				
Number of foldings								
50,000 times		100,000 times		50,000 times		100,000 times		
Presence/absence of pattern								
	○	X	○	X	○	X	○	X
DT(ΔV_{th})	0.008	-0.156	0.133	-0.604	-0.005	0.112	0.000	-0.360
ST(ΔV_{th})	-0.000	-0.088	0.019	-0.347	0.041	-0.043	0.005	-0.085

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De is large. However, even if the threshold voltages V_{th} of the second, third, fourth, fifth, and sixth transistors T2, T3, T4, T5, and T6 are changed, the current variability of the light-emitting diode De is not large.

Accordingly, the first shield pattern **122a** of the non-folding region NFR is formed to overlap the driving transistor DT and the first transistor T1 of each sub-pixel.

On the other hand, as described above, the second shield pattern **122b** of the folding region FR is formed over substantially the whole of each sub-pixel and overlaps the

As shown in Table 2, it can be seen that the threshold voltage fluctuation range of the driving transistor DT is larger than that of the switching transistor ST.

In addition, it can be seen that the threshold voltage fluctuation range of the driving transistor DT increases as the radius of curvature decreases and increases as the number of foldings increases.

Meanwhile, it can be seen that the threshold voltage fluctuation range of the driving transistor DT is very small when there is the shield pattern thereunder compared to the case where there is no shield pattern thereunder.

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As described above, in the present disclosure, the shield pattern is designed differently in the folding region and the non-folding region. That is, the first shield pattern is formed under the driving transistor DT of the non-folding region, and the second shield pattern is formed over substantially the entire surface of the folding region. Accordingly, it is possible to improve the durability in the folding region and to prevent deterioration of the driving characteristics due to the parasitic capacitance in the non-folding region.

Further, the plurality of openings is provided in the folding region of the plate bottom for improving the durability and maintaining the shape, so that the folding characteristics can be improved.

It will be apparent to those skilled in the art that various modifications and variations can be made in the foldable display device of the present disclosure without departing from the technical idea or scope of the disclosure. Thus, it is intended that the present disclosure cover the modifications and variations of this disclosure provided they come within the scope of the appended claims and their equivalents.

What is claimed is:

1. A foldable display device, comprising:
 - a display panel including a plurality of sub-pixels and having a first shield pattern in a non-folding region and a second shield pattern in a folding region; and
 - a cover window over the display panel, wherein an area of the second shield pattern is larger than an area of the first shield pattern, wherein each of the plurality of sub-pixels includes a first transistor and a second transistor, wherein the first shield pattern overlaps the first transistor and is spaced apart from the second transistor, and wherein the second shield pattern overlaps the first transistor and the second transistor.
2. The foldable display device of claim 1, wherein the first shield pattern corresponds to one of the plurality of sub-pixels in the non-folding region, and the second shield pattern corresponds to all of the plurality of sub-pixels in the folding region.
3. The foldable display device of claim 1, wherein each of the plurality of sub-pixels includes a plurality of transistors including the first and second transistors, a storage capacitor, and a light-emitting diode, and wherein the first shield pattern overlaps some of the plurality of transistors including the first transistor, and the second shield pattern overlaps all of the plurality of transistors including the first and second transistors.
4. The foldable display device of claim 1, wherein the plurality of transistors includes a driving transistor and third,

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fourth, fifth, and sixth transistors, and the first transistor is connected to a gate electrode and a drain electrode of the driving transistor, and

wherein the first shield pattern overlaps the driving transistor and the first transistor, and the second shield pattern overlaps the driving transistor and the first, second, third, fourth, fifth, and sixth transistors.

5. The foldable display device of claim 4, wherein the second shield pattern further overlaps the storage capacitor and the light-emitting diode.

6. The foldable display device of claim 1, further comprising a plate bottom disposed under the display panel, wherein the plate bottom has a plurality of openings in the folding region.

7. The foldable display device of claim 6, wherein each of the plurality of openings has a first length of a first direction and a second length of a second direction greater than the first length, and

wherein the foldable display device is configured to be folded along the first direction.

8. The foldable display device of claim 6, wherein the display panel includes a display area where the plurality of sub-pixels is disposed to display an image and a non-display area surrounding the display area, and

wherein the plurality of openings is disposed in the display area of the folding region and in the non-display area.

9. The foldable display device of claim 8, wherein a gate driving part is provided in the non-display area of the display panel, and

wherein the plurality of openings overlaps the gate driving part.

10. The foldable display device of claim 9, wherein the second shield pattern overlaps the gate driving part.

11. The foldable display device of claim 6, further comprising:

a back plate between the display panel and the plate bottom; and

a plate top between the back plate and the plate bottom.

12. The foldable display device of claim 11, further comprising:

a polarizing plate between the display panel and the cover window; and

a decoration film between the polarizing plate and the cover window.

13. The foldable display device of claim 1, wherein the first and second shield patterns are formed of a metal material.

14. The foldable display device of claim 13, wherein the first and second shield patterns are electrically connected to a power line.

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